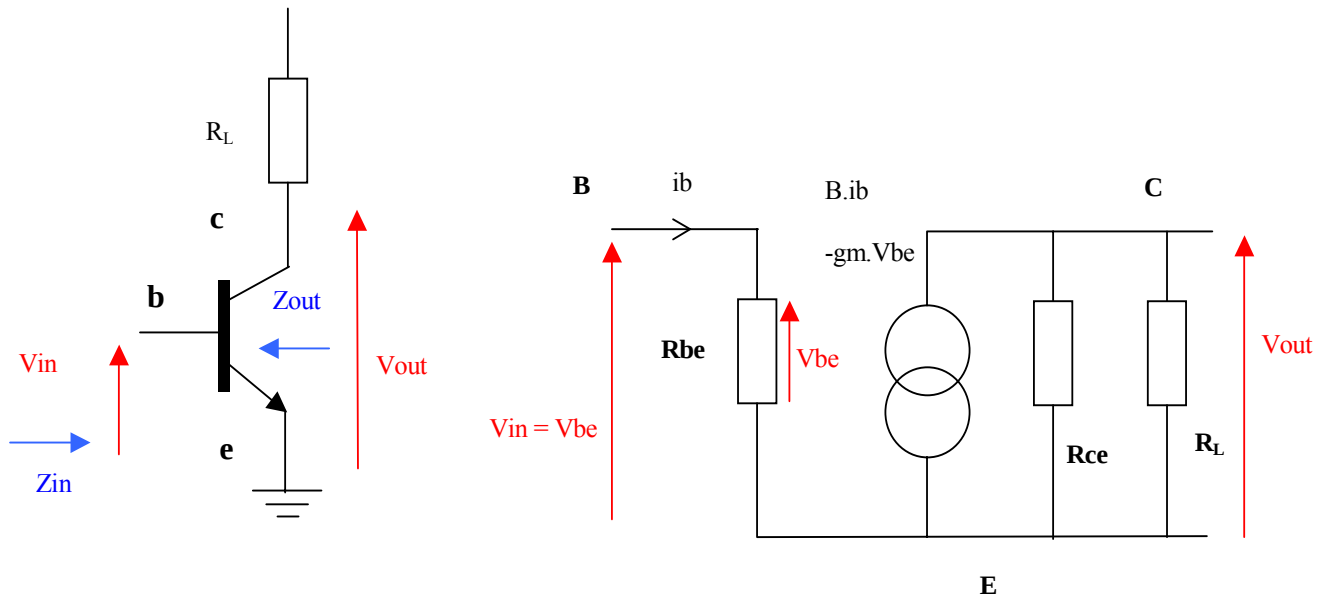


Common-Emitter/Source Circuits

Common-emitter BJT circuit

The figure below shows the simplified 'Pi' model of a common-emitter BJT.



$$R_{IN} = \frac{\beta}{gm} \quad \text{where } gm = \frac{I_{CQ}}{V_T} ; \quad V_T = \frac{k \cdot T}{q} \quad \text{where } k = \text{Boltzmann constant} = 1.3807 \times 10^{-23} \text{ JK}^{-1}$$

$$q = \text{Electron charge} = 1.6022 \times 10^{-19} \text{ C}$$

$$T = \text{Temperature in Kelvin}$$

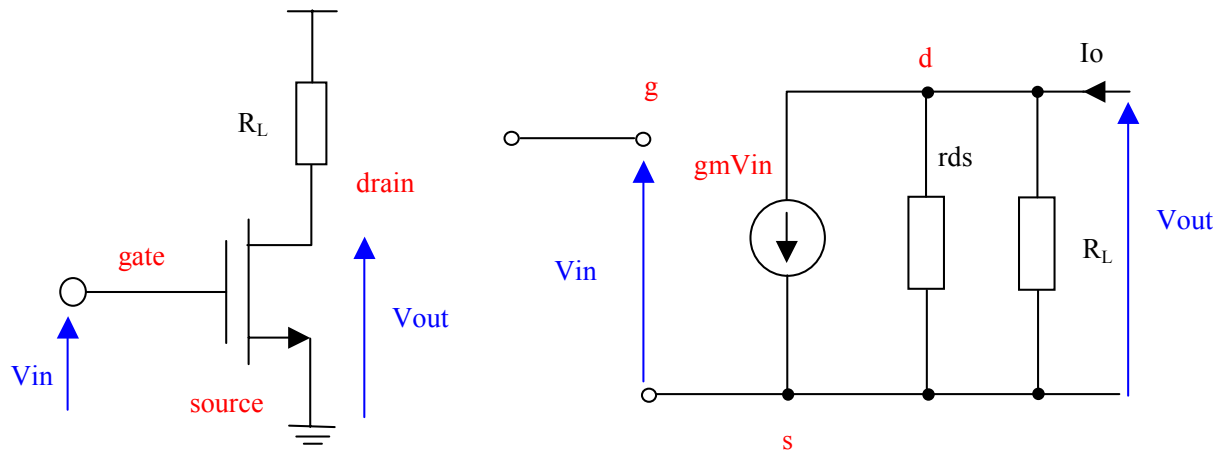
$$gm = \text{Transconductance (mS)}$$

$$R_{OUT} = r_{ce} = \frac{V_A}{I_{CQ}} \quad \text{Where } V_A = \text{Early Voltage (V)}$$

$$A_V = \frac{V_{OUT}}{V_{IN}} = \frac{-gm \cdot V_{be} \cdot r_{ce}}{V_{be}} = -gm \cdot r_{ce} = \frac{I_{CQ}}{V_T} \cdot \frac{V_A}{I_{CQ}} = \frac{V_A}{V_T}$$

$$A_I = \frac{I_{OUT}}{I_{IN}} = \frac{-\beta \cdot i_b}{i_b} = -\beta$$

Common-Source MOS FET Circuit



Voltage Gain A_v

$$A_v = \frac{V_o}{V_{in}}$$

$$V_o = -gmV_{in}(r_{ds} // R_L) \quad A = -gm \left(\frac{r_{ds} \cdot R_L}{r_{ds} + R_L} \right)$$

Input Resistance

$$R_{in} = \infty$$

Output Resistance

$$R_{out} = \frac{V_o}{I_o} = r_{ds} // R_L$$

Current Gain A_i

$$A_i = \infty$$